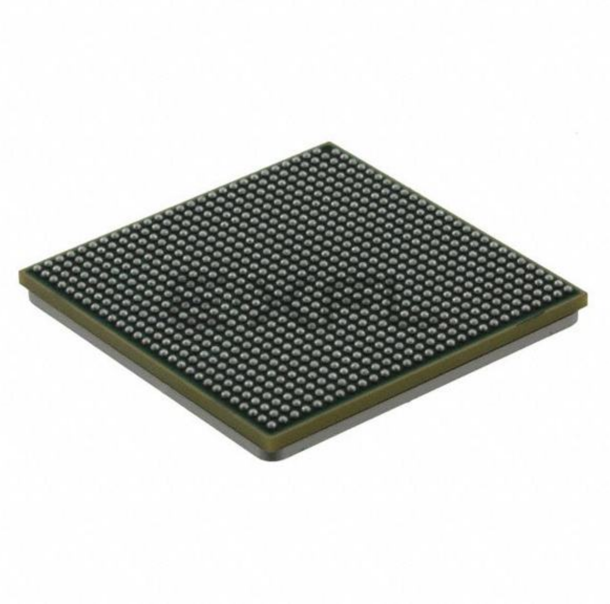

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8543vuang

NOTE

From a system standpoint, if any of the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the device.

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.15	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.15	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0\ V \leq V_{OUT} \leq GV_{DD}$.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

Table 37. MII Management AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC fall time	t_{MDHF}	—		10	ns	4

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the eTSEC system clock speed, which is half of the Platform Frequency (f_{CCB}). The actual ECn_MDC output clock frequency for a specific eTSEC port can be programmed by configuring the MgmtClk bit field of device's MIICFG register, based on the platform (CCB) clock running for the device. The formula is: Platform Frequency (CCB) ÷ (2 × Frequency Divider determined by MIICFG[MgmtClk] encoding selection). For example, if MIICFG[MgmtClk] = 000 and the platform (CCB) is currently running at 533 MHz, f_{MDC} = 533) ÷ (2 × 4 × 8) = 533) ÷ 64 = 8.3 MHz. That is, for a system running at a particular platform frequency (f_{CCB}), the ECn_MDC output clock frequency can be programmed between maximum $f_{MDC} = f_{CCB} \div 64$ and minimum $f_{MDC} = f_{CCB} \div 448$. See 14.5.3.6.6, "MII Management Configuration Register (MIIMCFG)," in the *MPC8548E PowerQUICC™ III Integrated Processor Family Reference Manual* for more detail.
3. The maximum ECn_MDC output clock frequency is defined based on the maximum platform frequency for device (533 MHz) divided by 64, while the minimum ECn_MDC output clock frequency is defined based on the minimum platform frequency for device (333 MHz) divided by 448, following the formula described in Note 2 above.
4. Guaranteed by design.
5. t_{CCB} is the platform (CCB) clock period.

Figure 21 shows the MII management AC timing diagram.

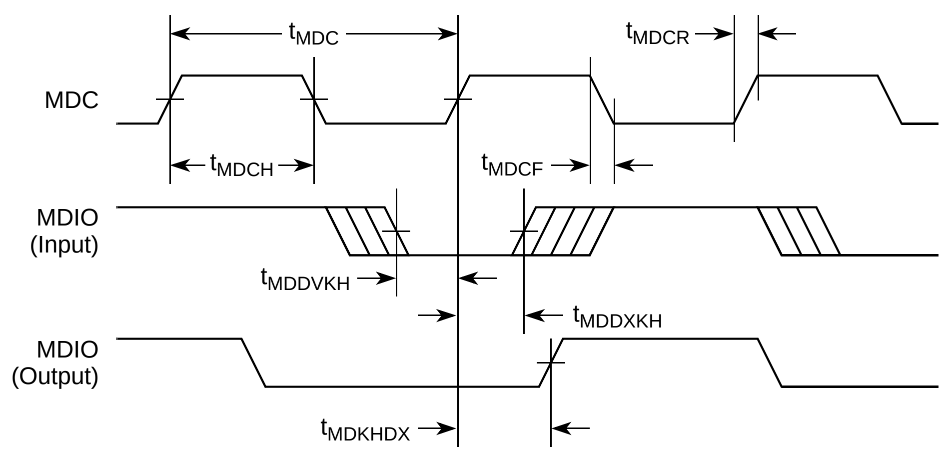


Figure 21. MII Management Interface Timing Diagram

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the device.

10.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 3.3 V DC.

Table 38. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or V_{IN} = BV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 39 provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 2.5 V DC.

Table 39. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (V_{IN}[1] = 0 V or V_{IN} = BV_{DD})	I_{IH}	—	10	μA
	I_{IL}		–15	
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 1 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

10.2 Local Bus AC Electrical Specifications

This table describes the timing parameters of the local bus interface at BV_{DD} = 3.3 V. For information about the frequency range of local bus, see Section 20.1, “Clock Ranges.”

Table 40. Local Bus Timing Parameters (BV_{DD} = 3.3 V)—PLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[*n*]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

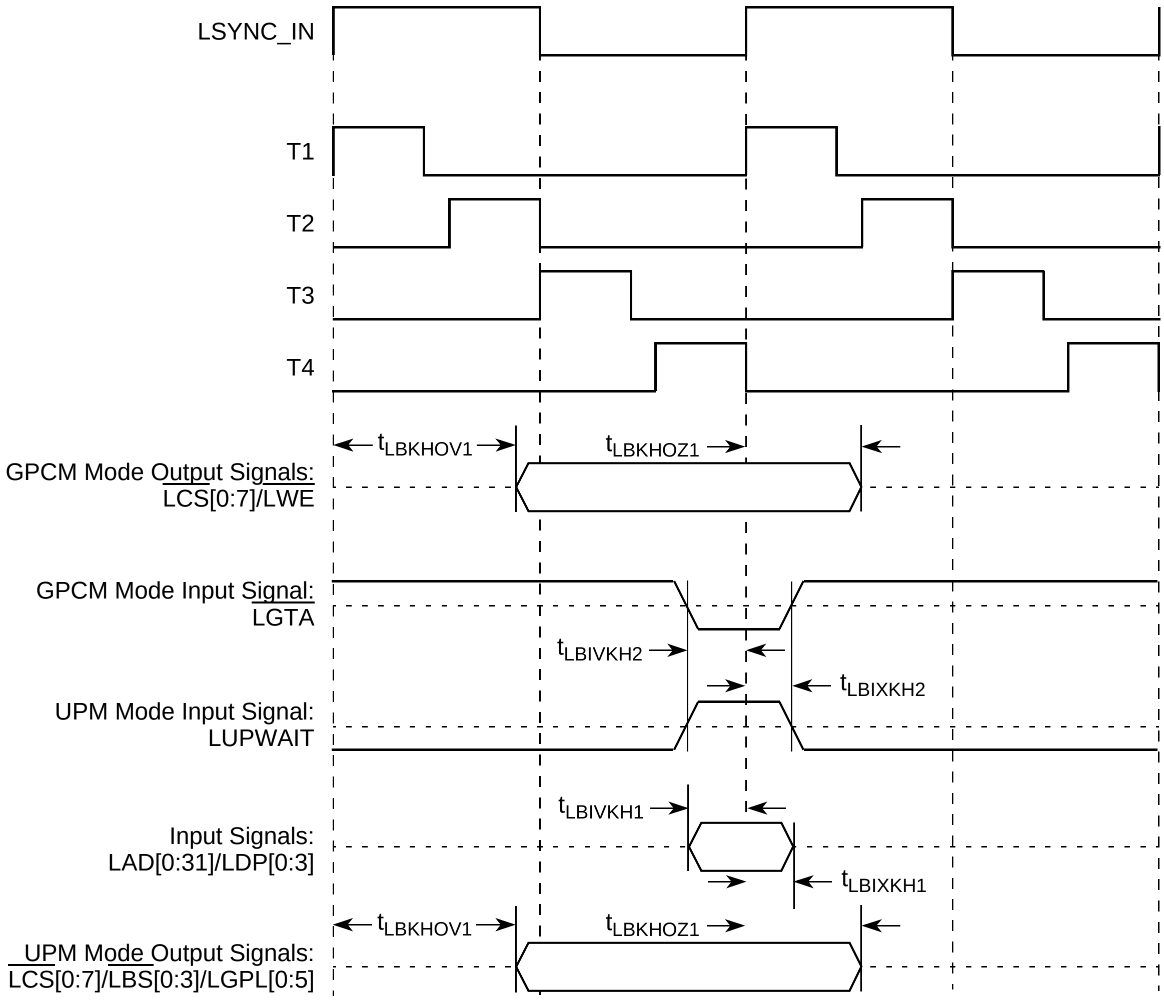


Figure 27. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Enabled)

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)[1] (continued)

Parameter	Symbol[2]	Min	Max	Unit	Notes
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 4 2	 20 10	ns	5
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 30 30	 — —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 3 3	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 29). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design.

Figure 29 provides the AC test load for TDO and the boundary-scan outputs.

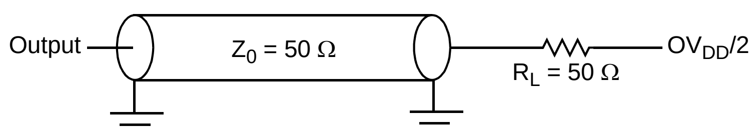


Figure 29. AC Test Load for the JTAG Interface

Figure 30 provides the JTAG clock input timing diagram.

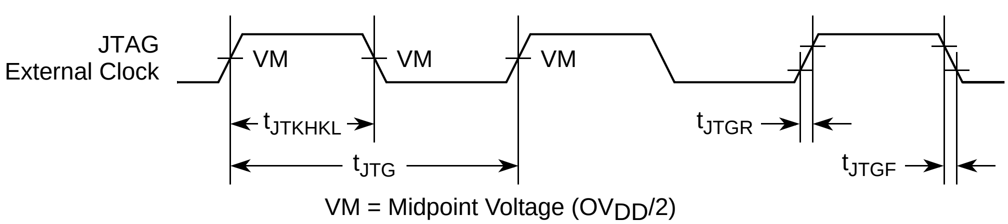


Figure 30. JTAG Clock Input Timing Diagram

14 GP_{OUT}/GP_{IN}

This section describes the DC and AC electrical specifications for the GP_{OUT}/GP_{IN} bus of the device.

14.1 GP_{OUT}/GP_{IN} Electrical Characteristics

Table 47 and Table 48 provide the DC electrical characteristics for the GP_{OUT} interface.

Table 47. GP_{OUT} DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3 V	BV_{DD}	3.13	3.47	V
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	BV_{DD} – 0.2	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.2	V

Table 48. GP_{OUT} DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 2.5 V	BV_{DD}	2.37	2.63	V
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	BV_{DD} + 0.3	V
Low-level output voltage (BV_{DD} min, I_{OL} = 1 mA)	V_{OL}	GND – 0.3	0.4	V

Table 49 and Table 50 provide the DC electrical characteristics for the GP_{IN} interface.

Table 49. GP_{IN} DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3 V	BV_{DD}	3.13	3.47	V
High-level input voltage	V_{IH}	2	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (BV_{IN} [1] = 0 V or BV_{IN} = BV_{DD})	I_{IN}	—	±5	μA

Note:
1. The symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

Table 53. PCI-X AC Timing Specifications at 66 MHz (continued)

Parameter	Symbol	Min	Max	Unit	Notes
$\overline{\text{HRESET}}$ to PCI-X initialization pattern hold time	t_{PCRHIX}	0	50	ns	6, 11

Notes:

1. See the timing measurement conditions in the *PCI-X 1.0a Specification*.
2. Minimum times are measured at the package pin (not the test point). Maximum times are measured with the test point and load circuit.
3. Setup time for point-to-point signals applies to $\overline{\text{REQ}}$ and $\overline{\text{GNT}}$ only. All other signals are bused.
4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Setup time applies only when the device is not driving the pin. Devices cannot drive and receive signals at the same time.
6. Maximum value is also limited by delay to the first transaction (time for $\overline{\text{HRESET}}$ high to first configuration access, t_{PCRHFV}). The PCI-X initialization pattern control signals after the rising edge of $\overline{\text{HRESET}}$ must be negated no later than two clocks before the first $\overline{\text{FRAME}}$ and must be floated no later than one clock before $\overline{\text{FRAME}}$ is asserted.
7. A PCI-X device is permitted to have the minimum values shown for t_{PCKHOV} and t_{CYC} only in PCI-X mode. In conventional mode, the device must meet the requirements specified in PCI 2.2 for the appropriate clock frequency.
8. Device must meet this specification independent of how many outputs switch simultaneously.
9. The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI-X 1.0a Specification.*
10. Guaranteed by characterization.
11. Guaranteed by design.

This table provides the PCI-X AC timing specifications at 133 MHz. Note that the maximum PCI-X frequency in synchronous mode is 110 MHz.

Table 54. PCI-X AC Timing Specifications at 133 MHz

Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	t_{PCKHOV}	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	t_{PCKHOX}	0.7	—	ns	1, 11
SYSCLK to output high impedance	t_{PCKHOZ}	—	7	ns	1, 4, 8, 12
Input setup time to SYSCLK	t_{PCIVKH}	1.2	—	ns	3, 5, 9, 11
Input hold time from SYSCLK	t_{PCIXKH}	0.5	—	ns	11
$\overline{\text{REQ64}}$ to $\overline{\text{HRESET}}$ setup time	t_{PCRVRH}	10	—	clocks	12
$\overline{\text{HRESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	12
$\overline{\text{HRESET}}$ high to first $\overline{\text{FRAME}}$ assertion	t_{PCRHFV}	10	—	clocks	10, 12
PCI-X initialization pattern to $\overline{\text{HRESET}}$ setup time	t_{PCIVRH}	10	—	clocks	12

Table 63. Long Run Transmitter AC Timing Specifications—2.5 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	800	1600	mVp-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	400	400	ps	±100 ppm

Table 64. Long Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	800	1600	mVp-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	320	320	ps	±100 ppm

For each baud rate at which an LP-serial transmitter is specified to operate, the output eye pattern of the transmitter shall fall entirely within the unshaded portion of the transmitter output compliance mask shown in Figure 52 with the parameters specified in Table 65 when measured at the output pins of the device and the device is driving a 100-Ω ± 5% differential resistive load. The output eye pattern of an LP-serial

Table 68. Receiver AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential input voltage	V_{IN}	200	1600	mVp-p	Measured at receiver
Deterministic jitter tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined deterministic and random jitter tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total jitter tolerance[1]	J_T	0.65	—	UI p-p	Measured at receiver
Multiple input skew	S_{MI}	—	22	ns	Skew at the receiver input between lanes of a multilane link
Bit error rate	BER	—	10^{-12}		—
Unit interval	UI	320	320	ps	±100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 53. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

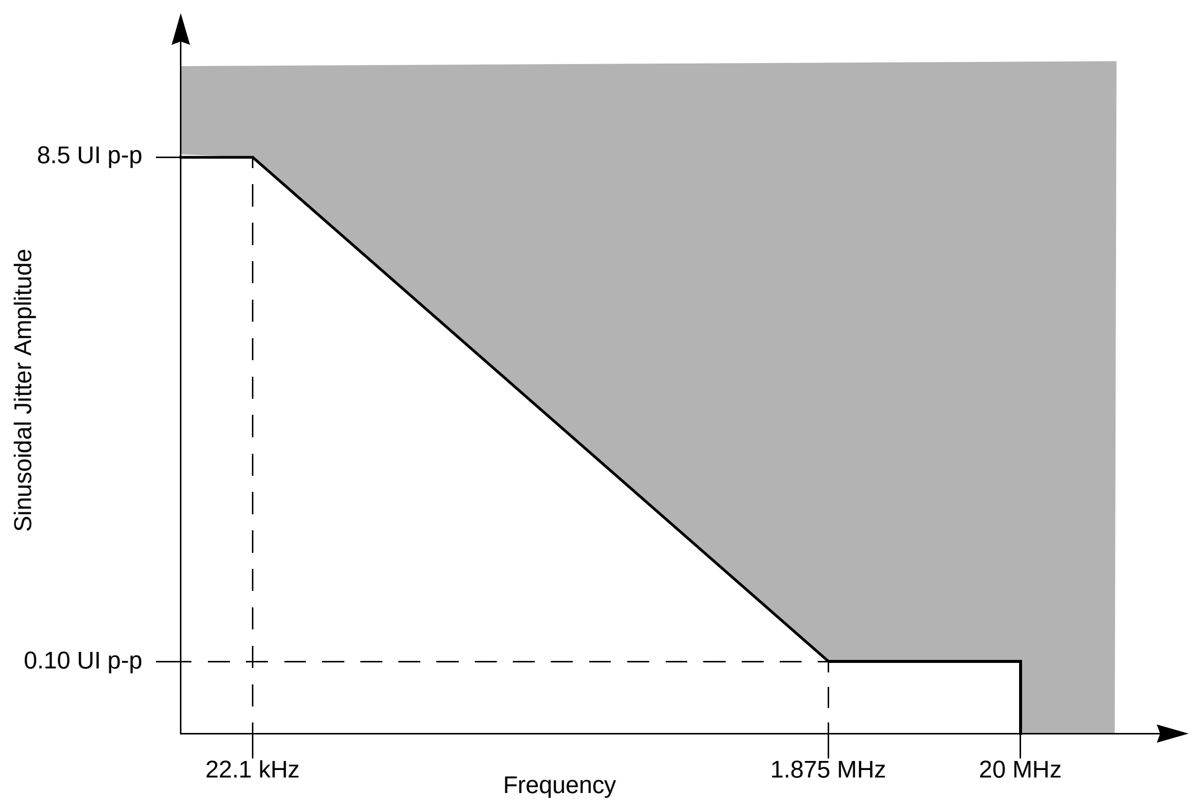


Figure 53. Single Frequency Sinusoidal Jitter Limits

Notes:

1. All dimensions are in millimeters.
2. Dimensioning and tolerancing per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
5. Parallelism measurement shall exclude any effect of mark on top surface of package.
6. All dimensions are symmetric across the package center lines unless dimensioned otherwise.

19.3 Pinout Listings

NOTE

The $\overline{\text{DMA\_DACK}}$[0:1] and TEST_SEL/$\overline{\text{TEST\_SEL}}$ pins must be set to a proper state during POR configuration. See the pinlist table of the individual device for more details.

For MPC8548/47/45, GPIOs are still available on PCI1_AD[63:32]/PC2_AD[31:0] pins if they are not used for PCI functionality.

For MPC8545/43, eTSEC does not support 16 bit FIFO mode.

Table 71 provides the pinout listing for the MPC8548E 783 FC-PBGA package.

Table 71. MPC8548E Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1 and PCI2 (One 64-Bit or Two 32-Bit)				
PCI1_AD[63:32]/PCI2_AD[31:0]	AB14, AC15, AA15, Y16, W16, AB16, AC16, AA16, AE17, AA18, W18, AC17, AD16, AE16, Y17, AC18, AB18, AA19, AB19, AB21, AA20, AC20, AB20, AB22, AC22, AD21, AB23, AF23, AD23, AE23, AC23, AC24	I/O	OV_{DD}	17
PCI1_AD[31:0]	AH6, AE7, AF7, AG7, AH7, AF8, AH8, AE9, AH9, AC10, AB10, AD10, AG10, AA10, AH10, AA11, AB12, AE12, AG12, AH12, AB13, AA12, AC13, AE13, Y14, W13, AG13, V14, AH13, AC14, Y15, AB15	I/O	OV_{DD}	17
PCI1_C_$\overline{\text{BE}}$[7:4]/PCI2_C_$\overline{\text{BE}}$[3:0]	AF15, AD14, AE15, AD15	I/O	OV_{DD}	17
PCI1_C_$\overline{\text{BE}}$[3:0]	AF9, AD11, Y12, Y13	I/O	OV_{DD}	17
PCI1_PAR64/PCI2_PAR	W15	I/O	OV_{DD}	
$\overline{\text{PCI1\_GNT}}$[4:1]	AG6, AE6, AF5, AH5	O	OV_{DD}	5, 9, 35
$\overline{\text{PCI1\_GNT0}}$	AG5	I/O	OV_{DD}	—
$\overline{\text{PCI1\_IRDY}}$	AF11	I/O	OV_{DD}	2
PCI1_PAR	AD12	I/O	OV_{DD}	—
$\overline{\text{PCI1\_PERR}}$	AC12	I/O	OV_{DD}	2
$\overline{\text{PCI1\_SERR}}$	V13	I/O	OV_{DD}	2, 4
$\overline{\text{PCI1\_STOP}}$	W12	I/O	OV_{DD}	2
$\overline{\text{PCI1\_TRDY}}$	AG11	I/O	OV_{DD}	2

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes

25. These are test signals for factory use only and must be pulled up (100 Ω–1 kΩ) to OV_{DD} for normal machine operation.
26. Independent supplies derived from board V_{DD}.
27. Recommend a pull-up resistor (~1 kΩ) be placed on this pin to OV_{DD}.
29. The following pins must NOT be pulled down during power-on reset: TSEC3_TXD[3], TSEC4_TXD3/TSEC3_TXD7, HRESET_REQ, TRIG_OUT/READY/QUIESCE, MSRCID[2:4], ASLEEP.
30. This pin requires an external 4.7-kΩ pull-down resistor to prevent PHY from seeing a valid transmit enable before it is actively driven.
31. This pin is only an output in eTSEC3 FIFO mode when used as Rx flow control.
32. These pins must be connected to XV_{DD}.
33. TSEC2_TXD1, TSEC2_TX_ER are multiplexed as cfg_dram_type[0:1]. They must be valid at power-up, even before HRESET assertion.
34. These pins must be pulled to ground through a 300-Ω (±10%) resistor.
35. When a PCI block is disabled, either the POR config pin that selects between internal and external arbiter must be pulled down to select external arbiter if there is any other PCI device connected on the PCI bus, or leave the PCI*n*_AD pins as 'no connect' or terminated through 2–10 kΩ pull-up resistors with the default of internal arbiter if the PCI*n*_AD pins are not connected to any other PCI device. The PCI block drives the PCI*n*_AD pins if it is configured to be the PCI arbiter—through POR config pins—irrespective of whether it is disabled via the DEVDISR register or not. It may cause contention if there is any other PCI device connected on the bus.
36. MDIC0 is grounded through an 18.2-Ω precision 1% resistor and MDIC1 is connected to GV_{DD} through an 18.2-Ω precision 1% resistor. These pins are used for automatic calibration of the DDR IOs.
38. These pins must be left floating.
39. If PCI1 or PCI2 is configured as PCI asynchronous mode, a valid clock must be provided on pin PCI1_CLK or PCI2_CLK. Otherwise the processor will not boot up.
40. These pins must be connected to GND.
101. This pin requires an external 4.7-kΩ resistor to GND.
102. For Rev. 2.x silicon, DMA_DACK[0:1] must be 0b11 during POR configuration; for rev. 1.x silicon, the pin values during POR configuration are don't care.
103. If these pins are not used as GPIN*n* (general-purpose input), they must be pulled low (to GND) or high (to LV_{DD}) through 2–10 kΩ resistors.
104. These must be pulled low to GND through 2–10 kΩ resistors if they are not used.
105. These must be pulled low or high to LV_{DD} through 2–10 kΩ resistors if they are not used.
106. For rev. 2.x silicon, DMA_DACK[0:1] must be 0b10 during POR configuration; for rev. 1.x silicon, the pin values during POR configuration are don't care.
107. For rev. 2.x silicon, DMA_DACK[0:1] must be 0b01 during POR configuration; for rev. 1.x silicon, the pin values during POR configuration are don't care.
108. For rev. 2.x silicon, DMA_DACK[0:1] must be 0b11 during POR configuration; for rev. 1.x silicon, the pin values during POR configuration are don't care.
109. This is a test signal for factory use only and must be pulled down (100 Ω – 1 kΩ) to GND for normal machine operation.
110. These pins must be pulled high to OV_{DD} through 2–10 kΩ resistors.
111. If these pins are not used as GPIN*n* (general-purpose input), they must be pulled low (to GND) or high (to OV_{DD}) through 2–10 kΩ resistors.
112. This pin must not be pulled down during POR configuration.
113. These should be pulled low or high to OV_{DD} through 2–10 kΩ resistors.

Table 72 provides the pin-out listing for the MPC8547E 783 FC-PBGA package.

NOTE

All note references in the following table use the same numbers as those for Table 71. See Table 71 for the meanings of these notes.

Table 72. MPC8547E Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1 (One 64-Bit or One 32-Bit)				
PCI1_AD[63:32]	AB14, AC15, AA15, Y16, W16, AB16, AC16, AA16, AE17, AA18, W18, AC17, AD16, AE16, Y17, AC18, AB18, AA19, AB19, AB21, AA20, AC20, AB20, AB22, AC22, AD21, AB23, AF23, AD23, AE23, AC23, AC24	I/O	OV_{DD}	17
PCI1_AD[31:0]	AH6, AE7, AF7, AG7, AH7, AF8, AH8, AE9, AH9, AC10, AB10, AD10, AG10, AA10, AH10, AA11, AB12, AE12, AG12, AH12, AB13, AA12, AC13, AE13, Y14, W13, AG13, V14, AH13, AC14, Y15, AB15	I/O	OV_{DD}	17
PCI1_C_$\overline{\text{BE}}$[7:4]	AF15, AD14, AE15, AD15	I/O	OV_{DD}	17
PCI1_C_$\overline{\text{BE}}$[3:0]	AF9, AD11, Y12, Y13	I/O	OV_{DD}	17
PCI1_PAR64	W15	I/O	OV_{DD}	—
$\overline{\text{PCI1\_GNT}}$[4:1]	AG6, AE6, AF5, AH5	O	OV_{DD}	5, 9, 35
$\overline{\text{PCI1\_GNT0}}$	AG5	I/O	OV_{DD}	—
$\overline{\text{PCI1\_IRDY}}$	AF11	I/O	OV_{DD}	2
PCI1_PAR	AD12	I/O	OV_{DD}	—
$\overline{\text{PCI1\_PERR}}$	AC12	I/O	OV_{DD}	2
$\overline{\text{PCI1\_SERR}}$	V13	I/O	OV_{DD}	2, 4
$\overline{\text{PCI1\_STOP}}$	W12	I/O	OV_{DD}	2
$\overline{\text{PCI1\_TRDY}}$	AG11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_REQ}}$[4:1]	AH2, AG4, AG3, AH4	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ0}}$	AH3	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	39
$\overline{\text{PCI1\_DEVSEL}}$	AH11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ64}}$	AF14	I/O	OV_{DD}	2, 5,10
$\overline{\text{PCI1\_ACK64}}$	V15	I/O	OV_{DD}	2
Reserved	AE28	—	—	2
Reserved	AD26	—	—	2
Reserved	AD25	—	—	2

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Reserved	AE26	—	—	2
cfg_pci1_clk	AG24	I	OV_{DD}	5
Reserved	AF25	—	—	101
Reserved	AE25	—	—	2
Reserved	AG25	—	—	2
Reserved	AD24	—	—	2
Reserved	AF24	—	—	2
Reserved	AD27	—	—	2
Reserved	AD28, AE27, W17, AF26	—	—	2
Reserved	AH25	—	—	2
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
$\overline{\text{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—
$\overline{\text{MWE}}$	E7	O	GV_{DD}	—
$\overline{\text{MCAS}}$	H7	O	GV_{DD}	—
$\overline{\text{MRAS}}$	L8	O	GV_{DD}	—
MCKE[0:3]	F10, C10, J11, H11	O	GV_{DD}	11
$\overline{\text{MCS}}$[0:3]	K8, J8, G8, F8	O	GV_{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV_{DD}	—
$\overline{\text{MCK}}$[0:5]	J9, A15, G1, L9, B14, F2	O	GV_{DD}	—
MODT[0:3]	E6, K6, L7, M7	O	GV_{DD}	—
MDIC[0:1]	A19, B19	I/O	GV_{DD}	36

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Local Bus Controller Interface				
LAD[0:31]	E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21	I/O	BV_{DD}	—
LDP[0:3]	K21, C28, B26, B22	I/O	BV_{DD}	—
LA[27]	H21	O	BV_{DD}	5, 9
LA[28:31]	H20, A27, D26, A28	O	BV_{DD}	5, 7, 9
$\overline{\text{LCS}}$[0:4]	J25, C20, J24, G26, A26	O	BV_{DD}	—
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	D23	I/O	BV_{DD}	1
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	G20	O	BV_{DD}	1
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	E21	O	BV_{DD}	1
$\overline{\text{LWE0}}$/$\overline{\text{LBS0}}$/LSDDQM[0]	G25	O	BV_{DD}	5, 9
$\overline{\text{LWE1}}$/$\overline{\text{LBS1}}$/LSDDQM[1]	C23	O	BV_{DD}	5, 9
$\overline{\text{LWE2}}$/$\overline{\text{LBS2}}$/LSDDQM[2]	J21	O	BV_{DD}	5, 9
$\overline{\text{LWE3}}$/$\overline{\text{LBS3}}$/LSDDQM[3]	A24	O	BV_{DD}	5, 9
LALE	H24	O	BV_{DD}	5, 8, 9
LBCTL	G27	O	BV_{DD}	5, 8, 9
LGPL0/LSDA10	F23	O	BV_{DD}	5, 9
LGPL1/$\overline{\text{LSDWE}}$	G22	O	BV_{DD}	5, 9
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LSDRAS}}$	B27	O	BV_{DD}	5, 8, 9
LGPL3/$\overline{\text{LSDCAS}}$	F24	O	BV_{DD}	5, 9
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/LPBSE	H23	I/O	BV_{DD}	—
LGPL5	E26	O	BV_{DD}	5, 9
LCKE	E24	O	BV_{DD}	—
LCLK[0:2]	E23, D24, H22	O	BV_{DD}	—
LSYNC_IN	F27	I	BV_{DD}	—
LSYNC_OUT	F28	O	BV_{DD}	—
DMA				
$\overline{\text{DMA\_DACK}}$[0:1]	AD3, AE1	O	OV_{DD}	5, 9, 107
$\overline{\text{DMA\_DREQ}}$[0:1]	AD4, AE2	I	OV_{DD}	—
$\overline{\text{DMA\_DDONE}}$[0:1]	AD2, AD1	O	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{UDE}}$	AH16	I	OV_{DD}	—
$\overline{\text{MCP}}$	AG19	I	OV_{DD}	—

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MDIC[0:1]	A19, B19	I/O	GV_{DD}	36
Local Bus Controller Interface				
LAD[0:31]	E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21	I/O	BV_{DD}	—
LDP[0:3]	K21, C28, B26, B22	I/O	BV_{DD}	—
LA[27]	H21	O	BV_{DD}	5, 9
LA[28:31]	H20, A27, D26, A28	O	BV_{DD}	5, 7, 9
LCS[0:4]	J25, C20, J24, G26, A26	O	BV_{DD}	—
LCS5/DMA_DREQ2	D23	I/O	BV_{DD}	1
LCS6/DMA_DACK2	G20	O	BV_{DD}	1
LCS7/DMA_DDONE2	E21	O	BV_{DD}	1
LWE0/LBS0/LSDDQM[0]	G25	O	BV_{DD}	5, 9
LWE1/LBS1/LSDDQM[1]	C23	O	BV_{DD}	5, 9
LWE2/LBS2/LSDDQM[2]	J21	O	BV_{DD}	5, 9
LWE3/LBS3/LSDDQM[3]	A24	O	BV_{DD}	5, 9
LALE	H24	O	BV_{DD}	5, 8, 9
LBCTL	G27	O	BV_{DD}	5, 8, 9
LGPL0/LSDA10	F23	O	BV_{DD}	5, 9
LGPL1/LSDWE	G22	O	BV_{DD}	5, 9
LGPL2/LOE/LSDRAS	B27	O	BV_{DD}	5, 8, 9
LGPL3/LSDCAS	F24	O	BV_{DD}	5, 9
LGPL4/LGTA/LUPWAIT/LPBSE	H23	I/O	BV_{DD}	—
LGPL5	E26	O	BV_{DD}	5, 9
LCKE	E24	O	BV_{DD}	—
LCLK[0:2]	E23, D24, H22	O	BV_{DD}	—
LSYNC_IN	F27	I	BV_{DD}	—
LSYNC_OUT	F28	O	BV_{DD}	—
DMA				
DMA_DACK[0:1]	AD3, AE1	O	OV_{DD}	5, 9, 106
DMA_DREQ[0:1]	AD4, AE2	I	OV_{DD}	—
DMA_DDONE[0:1]	AD2, AD1	O	OV_{DD}	—
Programmable Interrupt Controller				

Table 77. Processor Core Clocking Specifications (MPC8543E)

Characteristic	Maximum Processor Core Frequency				Unit	Notes
	800 MHz		1000 MHz			
	Min	Max	Min	Max		
e500 core processor frequency	800	800	800	1000	MHz	1, 2

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, "CCB/SYSCLK PLL Ratio," and Section 20.3, "e500 Core PLL Ratio," for ratio settings.

2.)The minimum e500 core frequency is based on the minimum platform frequency of 333 MHz.

Table 78. Memory Bus Clocking Specifications (MPC8548E and MPC8547E)

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	1000, 1200, 1333 MHz			
	Min	Max		
Memory bus clock speed	166	266	MHz	1, 2

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, "CCB/SYSCLK PLL Ratio," and Section 20.3, "e500 Core PLL Ratio," for ratio settings.
2. The memory bus speed is half of the DDR/DDR2 data rate, hence, half of the platform clock frequency.

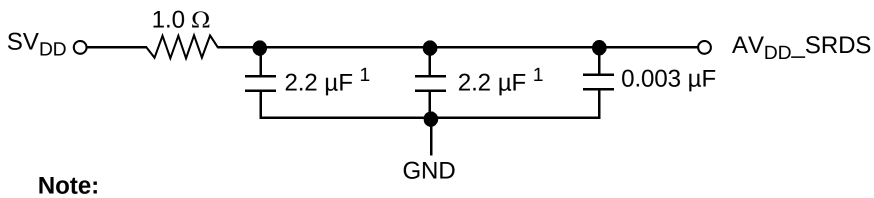
Table 79. Memory Bus Clocking Specifications (MPC8545E)

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	800, 1000, 1200 MHz			
	Min	Max		
Memory bus clock speed	166	200	MHz	1, 2

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, "CCB/SYSCLK PLL Ratio," and Section 20.3, "e500 Core PLL Ratio," for ratio settings.
2. The memory bus speed is half of the DDR/DDR2 data rate, hence, half of the platform clock frequency.

the ground plane. Use ceramic chip capacitors with the highest possible self-resonant frequency. All traces must be kept short, wide and direct.



Note:
1. An 0805 sized capacitor is recommended for system initial bring-up.

Figure 60. SerDes PLL Power Supply Filter

Note the following:

- AV_{DD}_SRDS must be a filtered version of SV_{DD}.
- Signals on the SerDes interface are fed from the XV_{DD} power plane.

22.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the device system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pin of the device. These decoupling capacitors must receive their power from separate V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND power planes in the PCB, utilizing short low impedance traces to minimize inductance. Capacitors must be placed directly under the device using a standard escape pattern as much as possible. If some caps are to be placed surrounding the part it must be routed with large trace to minimize the inductance.

These capacitors must have a value of 0.1 µF. Only ceramic SMT (surface mount technology) capacitors must be used to minimize lead inductance, preferably 0402 or 0603 sizes. Besides, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}, planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors must have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They must also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON). However, customers must work directly with their power regulator vendor for best values, types and quantity of bulk capacitors.

22.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors must be used to minimize inductance. Connections from all capacitors to power and ground must be done with multiple vias to further reduce inductance.